

isc Silicon NPN Power Transistor

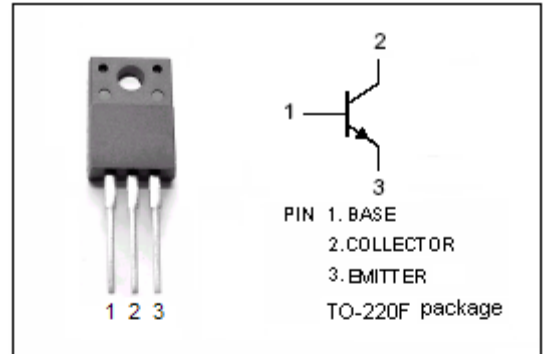
BUL312FP

DESCRIPTION

- Collector–Emitter Sustaining Voltage
: $V_{CEO(SUS)} = 500V(\text{Min.})$
- Low Collector Saturation Voltage
: $V_{CE(sat)} = 0.5V(\text{Max}) @ I_C = 1A$
- Very High Switching Speed

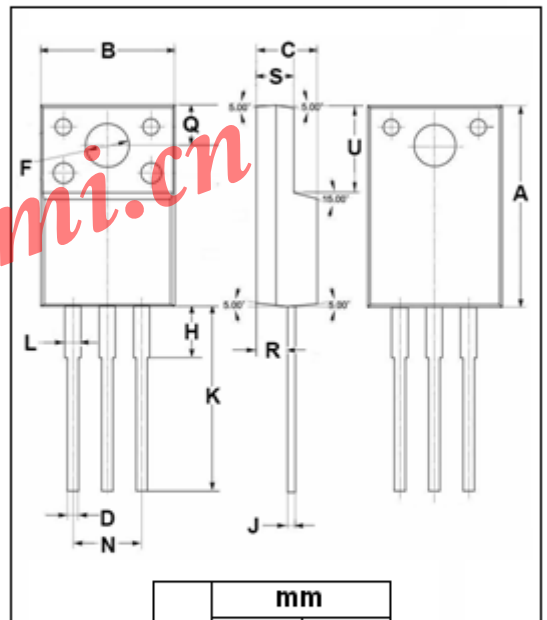
APPLICATIONS

- Designed for use in lighting applications and low cost switch-mode power supplies.



ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CES}	Collector-Emitter Voltage	1150	V
V_{CEO}	Collector-Emitter Voltage	500	V
V_{EBO}	Emitter-Base Voltage	9	V
I_C	Collector Current-Continuous	5	A
I_{CM}	Collector Current-peak $t_p < 5ms$	10	A
I_B	Base Current-Continuous	3	A
I_{BM}	Base Current-peak $t_p < 5ms$	4	A
P_C	Collector Power Dissipation $T_C=25^{\circ}C$	36	W
T_j	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-65~150	$^{\circ}C$



DIM	mm	
	MIN	MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.80
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.85
U	6.40	6.60

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	3.5	$^{\circ}C/W$
$R_{th j-A}$	Thermal Resistance, Junction to Ambient	62.5	$^{\circ}C/W$

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ELECTRICAL CHARACTERISTICS

 $T_C = 25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C = 100\text{mA}$; $L = 25\text{mH}$	500			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10\text{mA}$; $I_C = 0$	9			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C = 1\text{A}$; $I_B = 0.2\text{A}$			0.5	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C = 2\text{A}$; $I_B = 0.4\text{A}$			0.7	V
$V_{CE(sat)-3}$	Collector-Emitter Saturation Voltage	$I_C = 3\text{A}$; $I_B = 0.6\text{A}$			1.1	V
$V_{BE(sat)-1}$	Base-Emitter Saturation Voltage	$I_C = 1\text{A}$; $I_B = 0.2\text{A}$			1.0	V
$V_{BE(sat)-2}$	Base-Emitter Saturation Voltage	$I_C = 2\text{A}$; $I_B = 0.4\text{A}$			1.1	V
$V_{BE(sat)-3}$	Base-Emitter Saturation Voltage	$I_C = 3\text{A}$; $I_B = 0.6\text{A}$			1.2	V
I_{CES}	Collector Cutoff Current	$V_{CE} = 1150\text{V}$; $V_{BE} = 0$ $V_{CE} = 1150\text{V}$; $V_{BE} = 0$; $T_C = 125^\circ\text{C}$			1.0 2.0	mA
I_{CEO}	Collector Cutoff Current	$V_{CE} = 500\text{V}$; $I_B = 0$			0.25	mA
h_{FE-1}	DC Current Gain	$I_C = 10\text{mA}$; $V_{CE} = 5\text{V}$	8			
h_{FE-2}	DC Current Gain	$I_C = 3\text{A}$; $V_{CE} = 2.5\text{V}$		10		

Switching Times, Inductive Load

t_s	Storage Time	$I_C = 2\text{A}$; $V_{CL} = 250\text{V}$; $L = 200\ \mu\text{H}$; $I_{B1} = 0.4\text{A}$; $V_{BE(off)} = -5\text{V}$; $R_{BB} = 0\ \Omega$			1.9	μs
t_f	Fall Time				0.16	μs